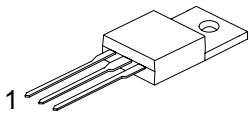
MBR1060C

DIODE

SCHOTTKY BARRIER RECTIFIER DIODES



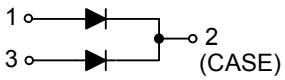
TO-220

*Pb-free plating product number: MBR1060CL

■ FEATURES

* Schottky Barrier Chip
* Guard Ring Die Construction for Transient Protection
* Low Power Loss, High Efficiency
* High Surge Capability
* High Current Capability and Low Forward Voltage Drop
* For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

■ SYMBOL



■ ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
MBR1060C-TA3-T	MBR1060CL-TA3-T	TO-220	A	K	A	Tube

Note: Pin Assignment: A: Anode K: Cathode

MBR1060CL-TA3-T

(1)Packing Type — (1) T: Tube

(2)Package Type — (2) TA3: TO-220

(3)Lead Plating — (3) L: Lead Free Plating Blank: Pb/Sn

■ ELECTRICAL CHARACTERISTICS RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Maximum Repetitive Peak Reverse Voltage		V_{RRM}	60	V
Maximum DC Blocking Voltage		V_R	60	V
Working Peak Reverse Voltage		V_{RWM}	60	V
Maximum PMS Reverse Voltage		$V_{R(RMS)}$	42	V
Average Forward Rectified Output Current (Note 1)(T_C=105°C)		I_{OUT}	10	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half-Sine-Wave		I_{FSM}	125	A
Repetitive Peak Reverse Surge Current (t_P≤ 2.0μs)		I_{RRM}	1.0	A
Forward Voltage Drop	I_F=5.0A, T_C=125°C	V_{FM}	0.70	V
	I_F=5.0A, T_C=25°C		0.80	V
	I_F=10A, T_C=25°C		0.95	V
Peak Reverse Current at Rated DC Blocking Voltage	T_C= 25°C	I_{RM}	0.1	mA
	T_C=125°C		15	mA
Typical Junction Capacitance (Note 2)		C_J	150	pF
Operating Temperature		T_J	-65 ~ +150	°C
Storage Temperature		T_{STG}	-65 ~ +150	°C

Notes: 1. Thermal resistance junction to case mounted heat sink.
2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.